

Performance

- Technology: 0.5um Power GaN HEMT
- Frequency: 1.2GHz
- Typical Pout : 49dBm(CW)
- Typical Gain: 14dB
- Typical PAE: 72%
- Bias: 28V/-2V~-3V
- Package: Metal Ceramic

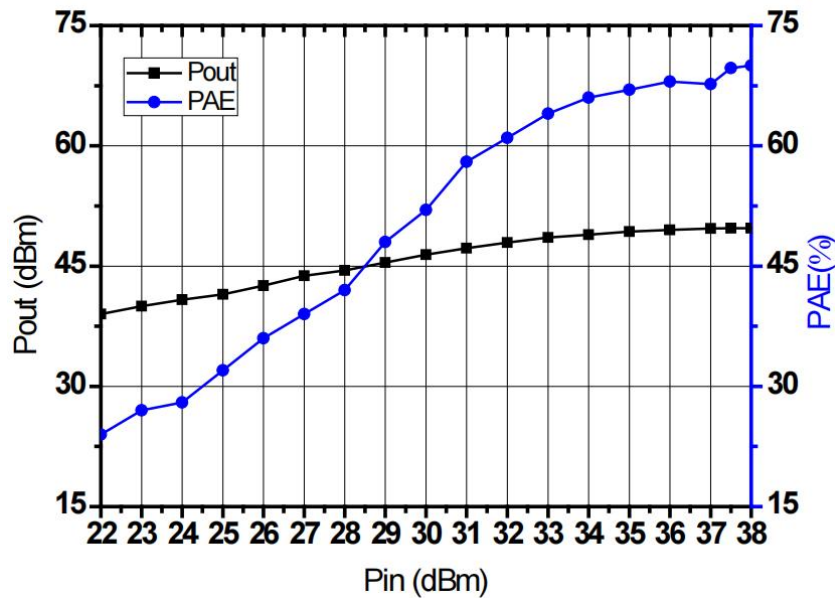


Electrical Specifications (TA=25°C, Vd=48V, Vg= -2.6V, PL=256us, D.C=50%, F: 1.15~1.35GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	49	-	dBm
Gp	Power Gain	-	14	-	dB
η_{add}	Power Added Efficiency	-	72	-	%
Rth	Thermal Resistance	-	-	1.3	°C/W

Test Curves

Pout&Pin@ Typ. point

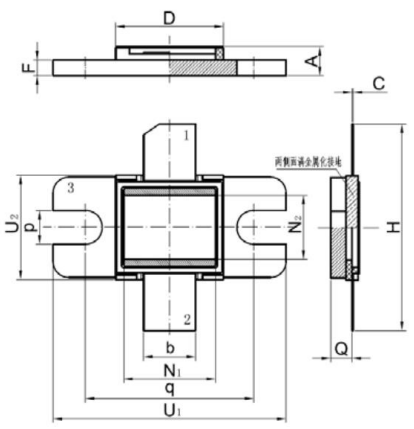


Absolute Max Ratings (TA=25°C)

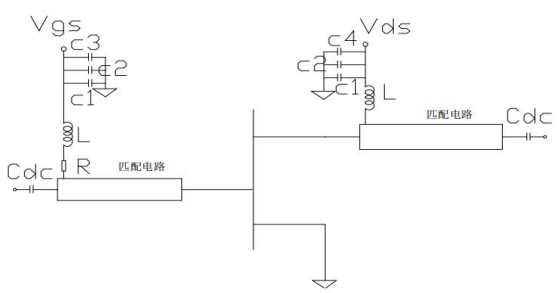
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	36V	
Vg	Grid Voltage	-5V	
Pd	DC Power	125W	25°C
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~150°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing

						
No	A	b	Q	q	U1	U2
Max.	5.02	5.21	2.32	16.64	22.99	10.29
Min.	-	4.95	1.92	16.38	22.73	10.03

Application Circuit

			
No	Value	No	Value
C1	100pF	Cdc	20pF
C2	1000pF	R	20Ω
C3	10uF	L	
C4	100uF		

Note:

- (1) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (2) In order to ensure the good performance of the power module, the capacity value of power filter and energy storage capacitor shall be reasonably selected according to the modulation mode during pulse operation.